2.4MHz 1A Step-Down Converter with I²C Interface

General Description

The RT5721 is a step-down switching voltage regulator that delivers a digitally programmable output from an input voltage supply of 2.5V to 5.5V. The output voltage is programmed through an I^2C interface capable of operating up to 3.4MHz.

Using a proprietary architecture with synchronous rectification, the RT5721 is capable of delivering 1A continuously at over 80% efficiency, maintaining that efficiency at load currents as low as 10mA. The regulator operates at a nominal fixed frequency of 2.4MHz, which reduces the value of the external components. Additional output capacitance can be added to improve regulation during load transients without affecting stability.

At moderate and light loads, Pulse Frequency Modulation (PFM) is used to operate in Power-Save Mode with a typical quiescent current of 45μ A at room temperature. Even with such a low quiescent current, the part exhibits excellent transient response during large load swings. At higher loads, the system automatically switches to fixed- frequency control, operating at 2.4MHz. In the Shutdown Mode, the supply current drops below 1μ A, reducing power consumption. The PFM Mode can be disabled if fixed frequency is desired. The RT5721 is available in a small WL-CSP-11B 1.31x1.62 (BSC).

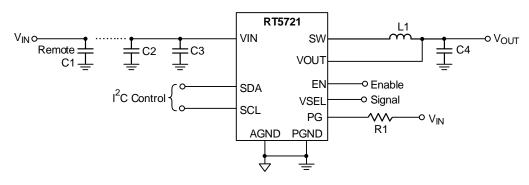
Features

- Steady 2.4MHz Switching Frequency
- Fast Load Transient
- Continuous Output Current Capability: 1A
- 2.5V to 5.5V Input Voltage Range
- Digitally Programmable Output Voltage
 - ► 0.3V to 1.3V Programmable Slew Rate for Voltage Transitions
- I²C-Compatible Interface Up to 3.4MHz
- PFM Mode for High Efficiency in Light Load
- Quiescent Current in PFM Mode: 45µA (Typical)
- Input Undervoltage Lockout (UVLO)
- Thermal Shutdown and Overload Protection
- Power Good Indicator

Applications

- Application, Graphic, and DSP Processors
 - ► ARMTM, TegraTM, OMAPTM, NovaThorTM, ARMADATM, KraitTM, etc.
- Hard Disk Drives, LPDDR3, LPDDR4
- Tablets, Netbooks, Ultra-Mobile PCs
- Smart Phones
- Gaming Devices

Simplified Application Circuit







Ordering Information

Product	Power-Up	Defaults	EN Dolov Timo	Paakaga Typa
Product	VSEL0	VSEL1	EN Delay Time	Package Type
RT5721AP-A	0.9V	0.8V	0ms	WL-CSP-11B 1.31x1.62 (BSC)

Note:

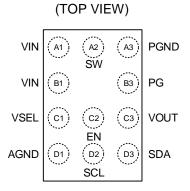
Richtek products are Richtek Green Policy compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.

Marking Information

CK: Product Code W: Date Code

СКШ

Pin Configuration



WL-CSP-11B 1.31x 1.62 (BSC)

Functional Pin Description

Pin No.	Pin Name	Pin Function
A1, B1	VIN	Power input voltage. Connect to the input power source. Connect to CIN with minimal path.
A2	SW	Switching node. Connect to the inductor.
A3	PGND	Power ground. The low-side MOSFET is referenced to this pin. CIN and COUT should be returned with a minimal path to these pins.
В3	PG	Power good indicator. The output of this pin is an open-drain with external pull-up resistor. After soft-startup, PG is pulled up when the FB voltage is within 87% (typ.). The PG status is low while EN is disabled. Note that when VIN is lower than 2.32V (typ.), the PG pin will keep low to indicate the power is not ready.
C1	VSEL	Voltage select. When this pin is low, VOUT is set by the VSEL0 register. When this pin is high, VOUT is set by the VSEL1 register. Polarity of this pin in conjunction with the mode bits in the Control register 02h will select Forced PWM or Auto PFM/PWM mode of operation.
C2	EN	Enable control input. A logic-high enables the converter; a logic-low forces the device into shutdown mode, and will reset all registers to the default value.
C3	VOUT	VOUT. Output voltage sense through this pin. Connect to output capacitor.
D1	AGND	Analog ground. All signals are referenced to this pin. Avoid routing high dV/dt AC currents through this pin.

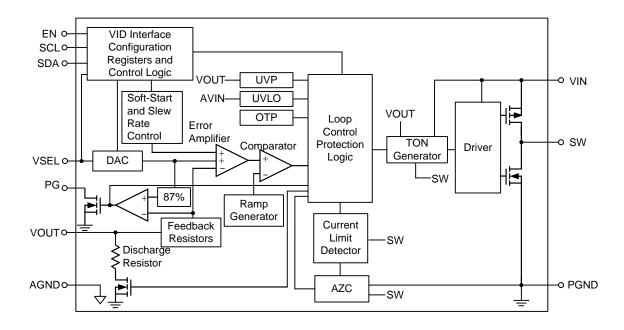


Pin No.	Pin Name	Pin Function	
D2	SCL	l ² C serial clock.	
D3	SDA	l ² C serial data.	





Functional Block Diagram



Copyright © 2023 Richtek Technology Corporation. All rights reserved. www.richtek.com

RT5721

Absolute Maximum Ratings (Note 1)

Supply Input Voltage, VIN	0.3V to 7V
Switch Node Voltage	0.3V to 7.3V
<50ns	-5V to 8.5V
Other I/O Pins Voltages	0.3V to 7.3V
Junction Temperature	- 150°C
Lead Temperature (Soldering, 10 sec.)	- 260°C
Storage Temperature Range	- –65°C to 150°C

ESD Ratings (Note 2)

•	ESD Susceptibility	
	HBM (Human Body Model)	2kV

Recommended Operating Conditions (Note 3)

٠	Supply Input Voltage, VIN	2.5V to 5.5V
•	Junction Temperature Range	–40°C to 125°C

Thermal Information (Note 4 and Note 5)

	Thermal Parameter	WL-CSP-11B 1.31x1.62 (BSC)	Unit
ΑΙθ	Junction-to-ambient thermal resistance (JEDEC standard)	49.9	°C/W
θJC(Top)	Junction-to-case (top) thermal resistance	2.1	°C/W
θ JC(Bottom)	Junction-to-case (bottom) thermal resistance	1.9	°C/W
θJA(EVB)	Junction-to-ambient thermal resistance (specific EVB)	65.4	°C/W
ΨJC(Top)	Junction-to-top characterization parameter	2.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	41.1	°C/W



Electrical Characteristics

(V_{IN} = 3.6V, T_A = 25°C, unless otherwise specified)

Paran	neter	Symbol	Test Conditions	Min	Тур	Max	Unit
Operating Qui Current PWM		IQ_PWM	I _{LOAD} = 0, mode Bit = 1 (Forced PWM)		15		mA
Operating Qui Current PFM	escent	IQ_PFM	Iload = 0		45		μA
H/W Shutdow Current	n Supply	ISHDN_H/W	EN = GND		0.1	3	μA
S/W Shutdown	n Supply	ISHDN_S/W	$EN = V_{IN}, 0x06[1:0] = 2b00,$ 2.5V $\leq V_{IN} \leq 5.5V$		2	12	μA
Undervoltage Threshold	Lockout	Vuvlo	V _{IN} rising		2.32	2.45	V
Undervoltage Hysteresis	Lockout	ΔVuvlo			350		mV
High-Side Swi Resistance	itch-On	RDS(ON)_H	V _{IN} = 5V		60		mΩ
Low-Side Swit Resistance	tch-On	RDS(ON)_L	VIN = 5V		34		mΩ
Enable Threshold	Logic-High	Viн	$2.5V \leq V_{IN} \leq 5.5V$	0.74	0.9	1.06	V
Voltage	Logic-Low	VIL	$2.5V \leq V \text{IN} \leq 5.5V$	0.64	0.8	0.92	
Enable Input E	Bias Current	IEN	EN Pin tied to GND or VIN		0.01	1	μA
VOUT DC Acc			$2.5V \le V_{IN} \le 5.5V$, Vout from minimum to maximum, IOUT(DC) = 0A to 1A, Auto PFM/PWM (Note 6)	-3		5	%
	Juracy		$2.5V \le V_{IN} \le 5.5V$, Vout from minimum to maximum, IOUT(DC) = 0A to 1A, Forced PWM (Note 6)	-1.5		1.5	%
Load Regulati	on	ΔV load	IOUT(DC) = 0.5A to 1A (Note 6)		0.1		%/A
Line Regulation	n	$\Delta VLINE$	$\begin{array}{l} 2.5V \leq V_{IN} \leq 5.5V, \\ I_{OUT(DC)} = 1A \mbox{(Note 6)} \end{array}$		0.2		%/V
Transient Loa	d Response	ACLOAD	ILOAD step 0.01A to 1A, tR = tF = 500ns, Vout = 1.125V (Note 6)		±45		mV
Transient Loa	d Response	ACLOAD	ILOAD step 0.01A to 0.8A, tr = tr = 1 μ s, L = 0.33 μ H, Cout = 22 μ F x 2 (Note 5)		45		mV
Line Transient	t	VLINE	$V_{IN} = 3V$ to 3.6V, $t_R = t_F = 10\mu s$, IOUT = 100mA, Forced PWM mode (Note 6)		±40		mV
High-Side MO Peak Current		ILIM_P			3.15		А
Low-Side MO Valley Current		ILIM_V			1.67		А
Thermal Shute	down	TSD			150		°C
Thermal Shute Hysteresis	down	ΔTSD			15		°C

Copyright © 2023 Richtek Technology Corporation. All rights reserved. **RICHTEK** is a registered trademark of Richtek Technology Corporation. www.richtek.com DS5721-00 November 2023



Param	neter	Symbol	Test Conditions	Min	Тур	Мах	Unit
Switching Free	quency	fsw		2100	2400	2700	kHz
Minimum Off-	Time	toff_min			170		ns
DAC Resolution	on		(Note5)		8		bits
DAC Different Nonlinearity	ial		(Note5)			0.5	LSB
Power Good							
Power Good T	brochold	Vth_pglh	VOUT rising, PGOOD from low to high		87		% of
Fower Good I	niesnoiu	Vth_pghl	VOUT falling, PGOOD from high to low		77		Vref
Power Good F Time	alling Delay				3		μs
I ² C Interface	(The I ² C inte	erface will no	ot work until the RESET# goes high) (N	ote 5)			
Param	neter	Symbol	Test Conditions	Min	Тур	Max	Unit
SDA, SCL	High Level			1.2			V
Input Voltage	Low Level					0.4	V
			Fast mode			400	kHz
SCL Clock Ra	te	fscl	Fast plus mode			1	MHz
			High speed mode, load 100pF max			3.4	MHz
Hold Time (Re			Fast mode	0.6			μs
Start Condition Period, the Fir		thd;STA	Fast plus mode	0.26			μs
Pulse is Gene			High speed mode	0.16			μs
			Fast mode	1.3			μs
Low Period of Clock	the SCL	tLOW	Fast plus mode	0.5			μs
Clock			High speed mode	0.16			μs
			Fast mode	0.6			μs
High Period of Clock	the SCL	t _{ніGH}	Fast plus mode	0.26			μs
Clock			High speed mode	0.06			μs
Set-Up Time f	or a		Fast mode	0.6			μs
Repeated ST/		tsu;sta	Fast plus mode	0.26			μs
Condition			High speed mode	0.01			μs
			Fast mode	0			μs
Data Hold Tim	e	thd;dat	Fast plus mode	0			μs
			High speed mode	0			μs
			Fast mode	100			ns
Data Set-Up T	ime	tsu;dat	Fast plus mode	50			ns
			High speed mode	10			ns





Parameter	Symbol	Test Conditions	Min	Тур	Мах	Unit
Set-Up Time for STOP Condition	tsu;sto	Fast mode	0.6			μs
		Fast plus mode	0.26			μs
Condition		High speed mode	0.16			μs
Bus Free Time between a	4	Fast mode	1.3			μs
STOP and START Condition	tBUF	Fast plus mode	0.5			μs
		Fast mode	20		300	ns
		Fast plus mode			120	ns
Rising Time of both SDA and SCL Signals	tR	High speed mode (SDA) load 100pF max	10		80	ns
		High speed mode (SCL) load 100pF max	10		40	ns
	tF	Fast mode	20×(V DD/5. 5V)		300	ns
Falling Time of both SDA and SCL Signals		Fast plus mode	20×(V DD/5. 5V)		120	ns
and SCL Signals		High speed mode (SDA) load 100pF max	10		80	ns
		High speed mode (SCL) load 100pF max	10		40	ns
SDA Output Low Sink Current	IOL	SDA voltage = 0.4V	2			mA
		Fast mode	20×(V DD/5. 5V)		300	ns
Falling Time of both SDA and SCL Signals	tF	Fast plus mode	20×(V DD/5. 5V)		120	ns
		High speed mode (SDA) load 100pF max	10		80	ns
		High speed mode (SCL) load 100pF max	10		40	ns
SDA Output Low Sink Current	IOL	SDA voltage = 0.4V	2			mA

Note 1. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Note 2. Devices are ESD sensitive. Handling precautions are recommended.

Note 3. The device is not guaranteed to function outside its operating conditions.

Note 4. For more information about thermal parameter, see the Application and Definition of Thermal Resistances report, AN061.

Note 5. θ_{JA(EVB)}, Ψ_{JC(Top)} and Ψ_{JB} are measured on a high effective-thermal-conductivity four-layer test board which is in size of 70mm x 50mm, furthermore, all layers with 1 oz. Thermal resistance/parameter values may vary depending on the PCB material, layout, and test environmental conditions.

Note 6. Guaranteed by design.

Typical Application Circuit

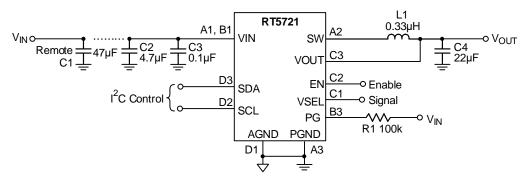


Table 1. Recommended External Components for 1A Maximum Load Current

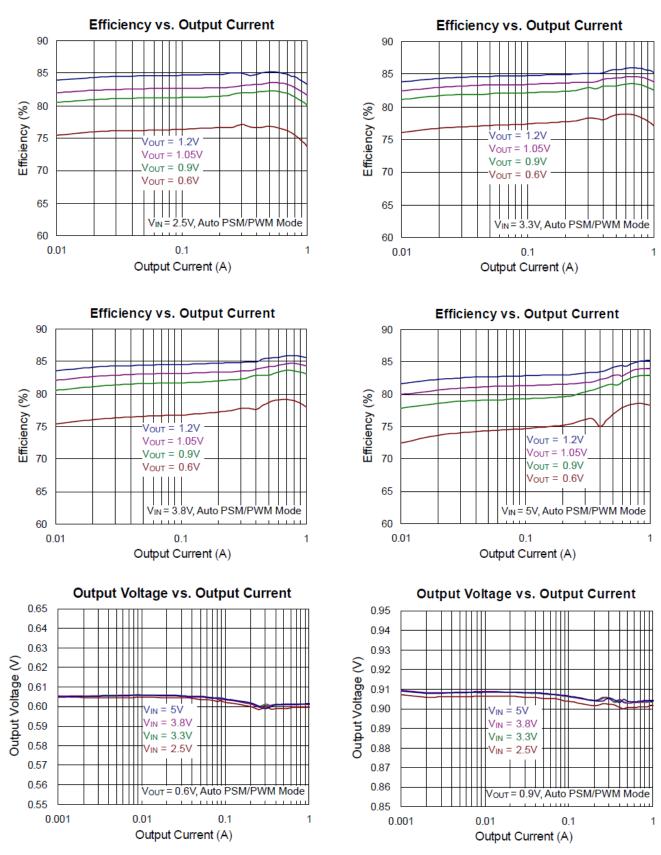
Component	Description	Vendor P/N
L1	330nH, 2016 case size	DFE201610E-R33M=P2 (Murata)
	SSUIT, 2010 Case Size	HMMQ20161T-33MDR (Cyntec)
C2	4.7μF, 10V, X5R, 0402	ZRB15XR61A475ME01D (Murata)
C3 ⁽¹⁾	100nF, 6.3V, X5R, 0201	GRM033R60J104KE19D (Murata)
C4	22μF, 6.3V, X5R, 0603	GRM188R60J226MEA0D (Murata)
C4 22μΓ, 6.3V, Λ5Κ, 0603	22μΓ, 0.3V, Λ3Κ, 0003	C1608X5R0J226M080AC (TDK)

Note:

- 1. The decoupling capacitor C3 is recommended to reduce any high frequency component on VIN bus.
- 2. All the input and output capacitors are the suggested values, referring to the effective capacitances, subject to any de-rating effect, like a DC bias.

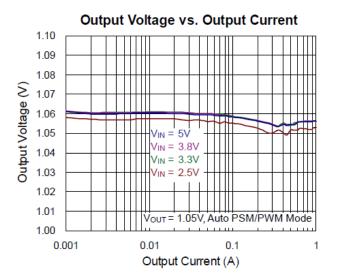
Typical Operating Characteristics

Unless otherwise specified, Auto PFM/PWM mode, T_A = 25°C; circuit and components according to typical application circuit and Table 2.

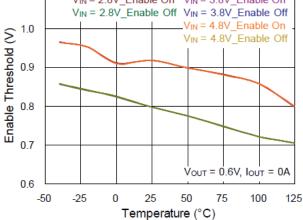


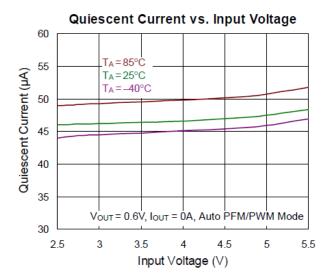
RICHTEK

1.1

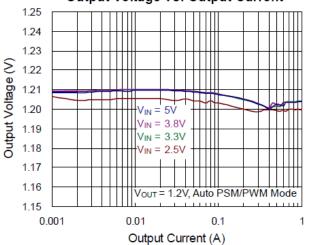




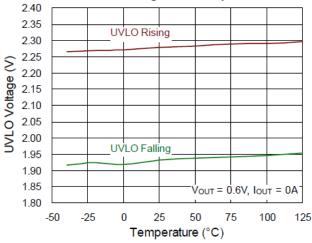


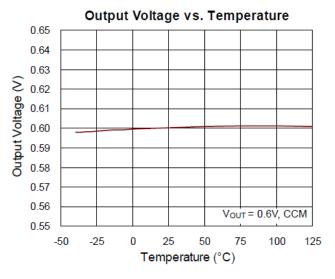


Output Voltage vs. Output Current



UVLO Voltage vs. Temperature





Copyright © 2023 Richtek Technology Corporation. All rights reserved.

RT5721

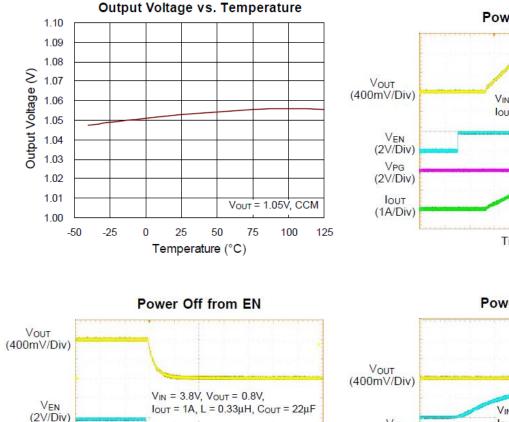
RT5721

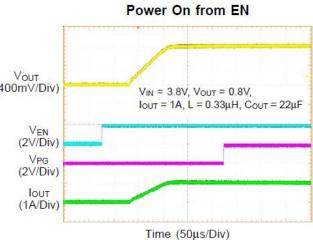
VPG

(2V/Div)

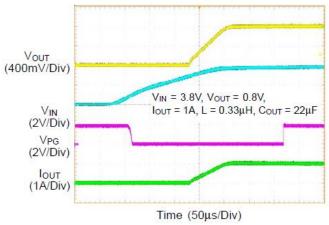
IOUT (1A/Div)

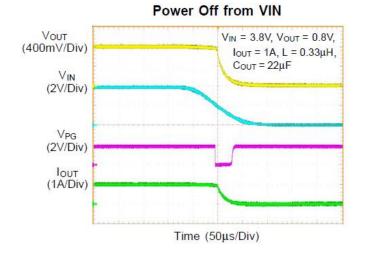
RICHTEK



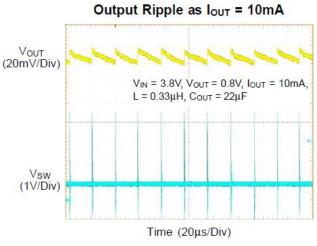


Power On from VIN





Time (50µs/Div)



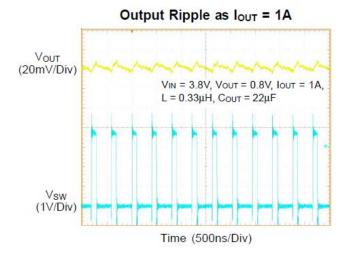
Copyright © 2023 Richtek Technology Corporation. All rights reserved. www.richtek.com

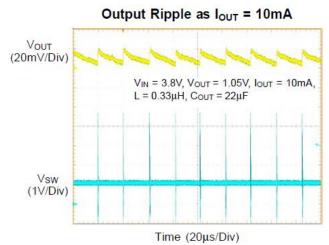
V_{OUT} (20mV/Div)

Vsw

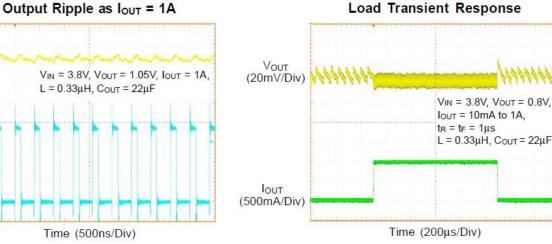
(1V/Div)

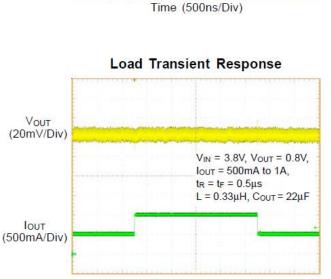
RT5721





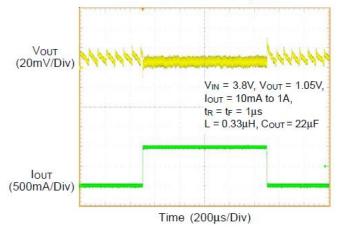
Load Transient Response







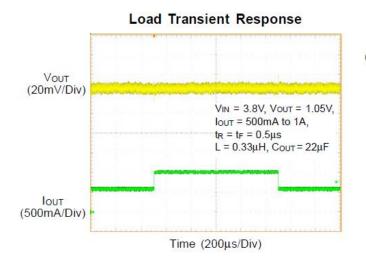
Load Transient Response



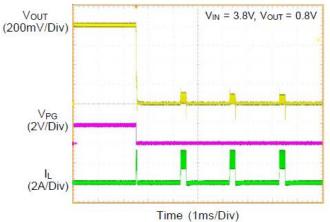
Copyright © 2023 Richtek Technology Corporation. All rights reserved. RICHTEK is a registered trademark of Richtek Technology Corporation.

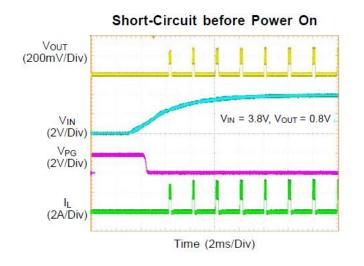
RT5721





Over-Current Protection





Operation

The RT5721 is a low voltage synchronous step-down converter that supports input voltage ranging from 2.5V to 5.5V and the output current can be up to 1A. The RT5721 uses ACOT[®] mode control. To achieve good stability with low-ESR ceramic capacitors, the ACOT[®] uses a virtual inductor current ramp generated inside the IC. This internal ramp signal replaces the ESR ramp normally provided by the output capacitor's ESR. The ramp signal and other internal compensations are optimized for low-ESR ceramic output capacitors.

In steady-state operation, the feedback voltage, with the virtual inductor current ramp added, is compared to the reference voltage. When the combined signal is less than the reference, the on-time one-shot is triggered, as long as the minimum off-time one-shot is cleared and the measured inductor current (through the synchronous rectifier) is below the current limit. The ontime one-shot turns on the high-side switch and the inductor current ramps up linearly. After the on-time, the high-side switch is turned off and the synchronous rectifier is turned on and the inductor current ramps down linearly. At the same time, the minimum off-time one-shot is triggered to prevent another immediate ontime during the noisy switching time and allows the feedback voltage and current sense signals to settle. The minimum off-time is kept short so that rapidlyrepeated on-times can raise the inductor current quickly when needed.

PWM Frequency and Adaptive On-Time Control

The on-time can be roughly estimated by the equation:

$$T_{ON} = \frac{V_{OUT}}{V_{IN}} \times \frac{1}{f_{SW}}$$

where fsw is nominal 2.4MHz.

Auto-Zero Current Detector

The auto-zero current detector circuit senses the SW waveform to adjust the zero current threshold voltage. When the current of low-side MOSFET decrease to the zero current threshold, the low-side MOSFET turns off to prevent negative inductor current. In this way, the zero current threshold can be adjusted for different conditions to get better efficiency.

Undervoltage Protection (UVLO)

The UVLO continuously monitors the voltage of VIN to make sure the device works properly. When the VCC is high enough to reach the high threshold voltage of UVLO, the step-down converter softly starts or prebiases to its regulated output voltage. When the VIN decreases to its low threshold (160mV hysteresis), the device will shut down.

Power Good Indication Pin

The RT5721 features an open-drain power-good output (PG) to monitor the output voltage status. The output delay of comparator prevents false flag operation for short excursions in the output voltage, such as during line and load transients. Pull-up PG with a resistor to VOUT or an external voltage below 5.5V. When VIN voltage rises above VUVLO, the power-good function is activated. After soft- start is finished, the PG pin is controlled by a comparator connected to the feedback signal Vout. If Vout rises above a power-good high threshold (VTH_PGLH) (typically 87% of the reference voltage), the PG pin will be in high impedance and VPG will be held high. Moreover, when VIN is above UVLO and device is powered on through EN pin, the PG pin will assert high within $300\mu s$ as soon as the V_{EN} is above logic-high threshold; in other words, the PG delay time is around 300µs from EN asserts to logic-high. When VOUT falls below the power-good low threshold (VTH PGHL) (typically 77% of the reference voltage), the PG pin will be pulled low after a certain delay (3µs, typically). Once being started-up, if any internal protection is triggered, PG will be pulled low to GND. The internal open-drain pull down device $(11\Omega, typically)$ will pull the PG pin low. The power good indication profile is shown in Table 1. Note that when VIN is lower than 2.32V (typically), the PG pin will keep low to indicate the power is not ready.

Copyright © 2023 Richtek Technology Corporation. All rights reserved. **RICHTEK** is a registered trademark of Richtek Technology Corporation.



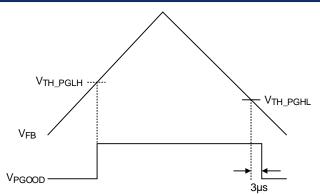


Figure 1. The Logic of PG

(Conditions	PG Pin					
Enable	Ven > Ven_h, Vfb > Vth_pglh	High Impedance					
Enable	Ven > Ven_h, Vfb < Vth_pghl	Low					
Shutdown	Ven < Ven_l	Low					
OTP	TJ > TSD	Low					

Table 2. PG Pin Status

Overcurrent Protection (OCP)

When the output voltage of the RT5721 is lower than 59% of the reference voltage after soft-start, the UVP is triggered.

The RT5721 senses the current signal when high-side and low-side MOSFET turns on. As a result, the OCP is cycle-by-cycle limit. If the OCP occurs, the converter holds off the next pulse and turns on low-side switch until inductor drops below the valley current limit, and then turns on high-side again to maintain output voltage and supports loading current to output before triggering UVP.

If the OCP condition keeps and the load current is larger than the current which converter can provide, the output voltage will decrease and drop below UVP threshold, and the converter will keep switching for 16 consecutive cycles before entering hiccup operation. The converter latches off 1.7ms when the output voltage is still lower than UVP threshold, and the soft-start sequence begins again after latching off time.

Soft-Start

An internal current source charges an internal capacitor to build the soft-start ramp voltage. The typical soft-start time can be programming by I^2C .

Over-Temperature Protection (OTP)

The RT5721 has over-temperature protection. When the device triggers the OTP, the device shuts down.

Overvoltage Behavior (OV)

The RT5721 provides a natural overvoltage protection function to prevent damage behavior during heavy load released scenario.

When device is set at auto PFM/PWM operation, the high-side and low-side MOSFET will automatically turn off immediately as long as output voltage rises above internal reference target. When the output voltage goes below the target, the internal comparator will trigger on-time controller to resume switching behavior to maintain excellent regulation.

When device is configured as FCCM operation mode, the high-side and low-side MOSFET will continuously switch to regulate the output voltage back to target setting.

Application Information

Richtek's component specification does not include the following information in the Application Information section. Thereby no warranty is given regarding its validity and accuracy. Customers should take responsibility to verify their own designs and reserve suitable design margin to ensure the functional suitability of their components and systems.

The basic RT5721 application circuit is shown in Typical Application Circuit. External component selection is determined by the maximum load current and begins with the selection of the inductor value and operating frequency followed by CIN and COUT.

Inductor Selection

The inductor value and operating frequency determine the ripple current according to a specific input and output voltage. The ripple current, ΔI_L , increases with higher VIN and decreases with higher inductance, as shown in the equation below:

$$\Delta I_{L} \!=\! \left[\frac{V_{OUT}}{f \times L} \right] \times \! \left[1 \!-\! \frac{V_{OUT}}{V_{IN}} \right]$$

where f is the operating frequency and L is the inductance.

To optimize the loop stability, 0.33µH is strongly

recommended. Suppose the higher inductance is chosen, the transient performance may become worse; in the opposite situation, the lower inductance causes larger ripple, and there is a risk of reaching negative overcurrent protection during VID down.

Input and Output Capacitor Selection

An input capacitor, CIN, is needed to filter out the trapezoidal current at the source of the high-side MOSFET.

To prevent large ripple current, a low ESR input capacitor sized for the maximum RMS current should be used. The RMS current is given by:

$$I_{RMS} = I_{OUT}(MAX) \times \frac{V_{OUT}}{V_{IN}} \times \sqrt{\frac{V_{IN}}{V_{OUT}}} - 1$$

This formula has a maximum at VIN = 2Vout, where IRMS = IOUT(MAX)/2.

This simple worst-case condition is commonly used for design.

Choose a capacitor rated at a higher temperature than

required. Several capacitors may also be paralleled to meet the size or height requirements of the design. Ceramic capacitors have high ripple current, high voltage rating and low ESR, which makes them ideal for switching regulator applications. However, they can also have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can lead to significant ringing. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input, VIN. At best, this ringing can couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at VIN large enough to damage the part. Thus, care must be taken to select a suitable input capacitor.

The selection of COUT is determined by the required ESR to minimize output voltage ripple. Moreover, the amount of bulk capacitance is also a key for COUT selection to ensure that the control loop is stable. Loop stability can be checked by viewing the load transient response.

The output voltage ripple, ΔV_{OUT} , is determined by:

$$\Delta V_{OUT} \leq \Delta I_{L} \left[\text{ESR} + \frac{1}{8 \times f_{SW} \times C_{OUT}} \right]$$

where fsw is the switching frequency and ΔI_L is the inductor ripple current. The output voltage ripple will be the highest at the maximum input voltage since ΔI_L increases with input voltage. Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirement.

Ceramic capacitors have excellent low ESR characteristics, but can have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can also lead to significant ringing.

Nevertheless, high value, low cost ceramic capacitors

RT5721

are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications.

I²C Interface Function

The RT5721 can be managed by I²C interface to select VOUT voltage level, Dynamic Voltage Scaling (DVS) slew rate, Auto PFM/PSM or Forced PWM mode, and so on.

The register of each function can be found from the following register map, which also explains how to use these functions.

VOUT Selection

The RT5721 has programmable VOUT from 0.3V to 1300mV with 5mV resolution.

The output voltage can be set by NSELx register bit and the output voltage is given by the following equation:

 $V_{OUT} = 0.3V + NSELx \times 5mV$

For example:

if NSELx = 0111100 (60 decimal), then

 $V_{OUT} = 0.3 + 60 \times 5 mV$

= 0.3 + 0.3 = 0.6V.

The RT5721 also has external VSEL pin to select

NSEL1(0X01) or NSEL0(0X00). Pulling VSEL to high is for VSEL1 and pulling VSEL to low is for VSEL0.

Upon POR, VSEL0 and VSEL1 are reset to their default voltages.

Enable and Soft-Start

When the EN pin is LOW, the IC is shut down, all internal circuits are off, and the part draws very little current. In this state, I2C cannot be written to or read until input voltage is above the UVLO. The registers are

reset when the EN pin is LOW or during a Power On Reset (POR).

Once the EN pin is high, VOUT will ramp up at the chosen soft-start slew rate programmed in the CONTROL2 register SS_SR bit.

Discharge Function

In the CONTROL1 register, setting the DISCHG bit to 1 can make VOUT discharge by internal resistor when the converter shuts down. If the DISCHG bit is set to 0, VOUT will decrease depending on the loading. When EN pin is set to low, the RT5721 turns on 11Ω discharge resistor by default.

Slew Rate Setting

The RT5721 can control slew rate as VOUT changes between two voltage levels for both up and down.

The UP_SR bits in the CONTROL1 register control upspeed, whereas the DN_SR bits in the CONTROL2 register control down-speed. The default DVS up slew rate is $12mV/\mu s$ and DVS down slew rate is $3mV/\mu s$.

Forced PWM Mode

The MODE_VSEL0 and MODE_VSEL1 bits in CONTROL1 register can determine the operation mode of the converter. Set 1 for Forced PWM operation and set 0 for auto PSM/PWM operation. Note that, MODE_VSEL0 is activated only when pulling VSEL pin to low, and only set VSEL pin to high for VSEL1 so that the setting of MODE_VSEL1 can be activated.

During dynamic voltage scaling from high setting of output voltage to low setting, the RT5721 makes transient in Forced PWM mode, and output voltage will decrease quickly.

Copyright © 2023 Richtek Technology Corporation. All rights reserved. **RICHTEK** is a registered trademark of Richtek Technology Corporation.

The RT5721 all series IC are able to support fast mode I^2C interface (bit rate 400kb/s). For example, the RT5721A default I^2C slave address is 7'b1010000. The write or read bit stream (N ≥1) is shown below:

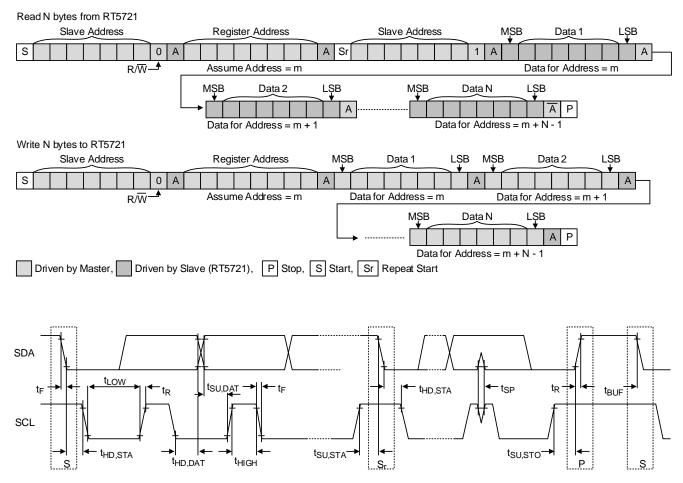


Figure 2. I²C Read and Write Stream and Timing Diagram

The RT5721 also supports High-speed mode (bit rate up to 3.4Mb/s) with access code 08H. Figure 3 and Figure 4 show detailed transfer format. Hs-mode can only commence after the following conditions (all of which are in F/S-mode):

- START condition (S)
- ▶ 8-bit master code (00001xxx)
- ▶ not-acknowledge bit (A)



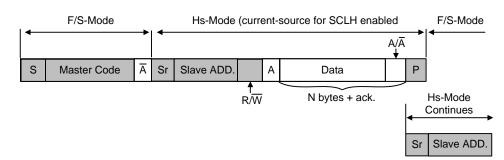


Figure 3. Data Transfer Format in Hs-mode

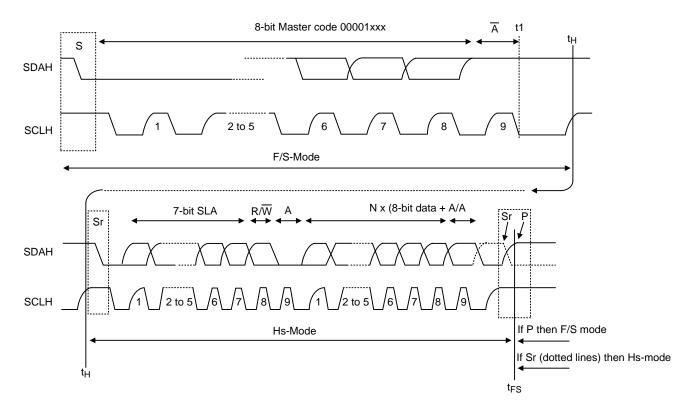


Figure 4. A Complete Hs-mode Transfer

Copyright © 2023 Richtek Technology Corporation. All rights reserved. **RICHTEK** is a registered trademark of Richtek Technology Corporation.



Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

$$PD(MAX) = (TJ(MAX) - TA)/\theta JA$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-toambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, $\theta_{JA(EVB)}$, is highly package dependent. For a WL-CSP-11B 1.31x1.62 (BSC) package, the thermal resistance, $\theta_{JA(EVB)}$, is 65.4°C/W on a high effective-thermal-conductivity four-layer test board. The maximum power dissipation at T_A = 25°C can be calculated as below:

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ})/(65.4^{\circ}C/W) = 1.53W$ for a WL-CSP-11B 1.31x1.62 (BSC) package.

The maximum power dissipation depends on the operating ambient temperature for the fixed T_J(MAX) and the thermal resistance, $\theta_{JA(EVB)}$. The derating curves in Figure 5 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

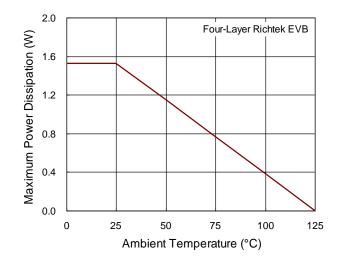


Figure 5. Derating Curve of Maximum Power Dissipation

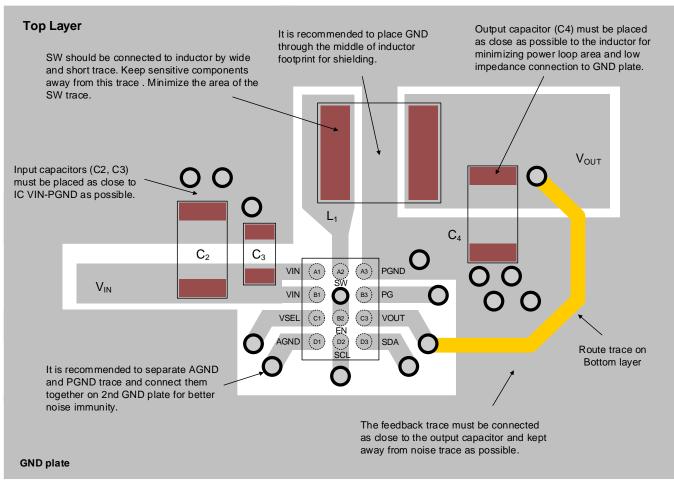
Layout Considerations

For best performance of the RT5721, the following layout guidelines must be strictly followed.

- Input capacitor must be placed as close as possible to IC to minimize the power loop area. A typical 0.1µF decoupling capacitor is recommended to reduce power loop area and any high frequency component on VIN.
- SW node is with high frequency voltage swing, so the SW node area should be kept small.
- Keep every power trace connected to pin as wide as possible for improving thermal dissipation.
- The AGND pin is suggested to connect to 2nd GND plate through top to 2nd via.









Copyright © 2023 Richtek Technology Corporation. All rights reserved.

Functional Register Description

	Table 3. Register Map											
Address	Register Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Default	Туре	
0x00	NSEL0				VSE	EL0				0x78	RW	
0x01	NSEL1				VSE	EL1				0x64	RW	
0x02	CONTRO L1	DISCHG	ι	UP_SR[2:0]			SW_ RESET	MODE_ VSEL1	MODE _VSE L0	0x90	R/W	
0x03	ID1	VE	VENDOR_ID Reserv DIE_ID					0x00	R			
0x04	ID2		Rese	erved			DIE_	REV		0x00	R	
0x05	MONITOR	PGOOD	UVLO	Reserv ed	POS	NEG	RESET _STAT	от	BUCK STAT US	0x00	R	
0x06	CONTRO L2	DI	N_SR[2:0	0] Reserv ed SS_SR[1:0] EN_ EN_V VSEL1 SEL0				0x63	R/W			
0x08	CONTRO L4	Reser	ved			DIS_D	LY[5:0]			0x00	R/W	

	Table 4. VSEL0									
	Address: 0x00 Description: Setting of VSEL0 voltage									
Bit	7	6	5	4	3	2	1	0		
Field				VSEI	_0					
Default (RT5721A)	0 1 1 1 1 0 0 0									
Туре				R/W	Ι					

Bit	Name	Description
7:0	NSEL0	VID Table satisfy : SEL[7:0] = 11001000 : VOUT = 1.3V SEL[7:0] = 00000000 : 0.3V 5mV step for 0.3V to 1.3V

Table 5. VSEL1

	Address: 0x01 Description: Setting of VSEL1 voltage										
Bit	7	6	5	4	3	2	1	0			
Field		VSEL1									
Default (RT5721A)	0	0 1 1 0 0 1 0 0									
Туре		R/W									

Bit	Name	Description
7:0	NSEL1	VID Table satisfy : SEL[7:0] = 1100100 0: VOUT = 1.3V SEL[7:0] = 00000000 : 0.3V 5mV step for 0.3V to 1.3V

Table	6.	CONTROL	1

Address: 0x02	
Description: Control1 setting	

Description:	Control1 setti	ng						
Bit	7	6	5	4	3	2	1	0
Field	DISCHG		UP_SR		Reserved	SW_ RESET	MODE_ VSEL1	MODE_ VSEL0
Default (RT5721A)	1	0	0	1	0	0	0	0
Туре	R/W		R/W		R/	W	R/	W

Bit	Name	Description				
7	DISCHG	0 : Discharge path disabled				
	DISCHG	1 : Discharge path enabled				
6:4	UP_SR[2:0]	DVS Speed for UP DVS 000 = 24mV step/µs 001 = 12mV step/µs 010 = 6mV step/µs 011 = 3mV step/µs 100 = 1.5mV step/µs 101 = 0.75mV step/µs 110 = 0.375mV step/µs 111 = 0.1875mV step/µs				
3	SW_RESET	write 1 to reset, always read 0				
2		0 : Auto				
2	MODE_VSEL1	1 : Continuous mode				
1		0 : Auto				
I	MODE_VSEL0	1 : Continuous mode				

Table 7. ID1

	Address: 0x03 Description: Search Vendor_ID and DIE_ID										
Bit	7	6	5	4	3	2	1	0			
Field	VE	ENDOR_ID[2	:0]	Reserved		DIE_I	2 1 0 DIE_ID[3:0] 0 0 0				
Default	0	0	0	0	0	0	0	0			
Туре		R		R		F	२				

Bit	Name	Description
7:5	VENDOR_ID	Vendor_ID
4	Reserved	Reserved bits
3:0	DIE_ID	DIE_ID

Table 8. ID2

Address: (Descriptio)x04 n: Search Re	evision_ID						
Bit	7	6	5	4	3	2	1	0
Field		Rese	erved			DIE_	REV	
Default	0	0	0	0	0	0	0	0
Туре	Type R R							

Bit	Name	Description
7:4	Reserved	Reserved bits
3:0	DIE_REV	Revision_ID

Table 9. MONITOR

Address: (Descriptio)x05 n: Monitoring	the IC statu	s					
Bit	7	6	5	4	3	2	1	0
Field	PGOOD	UVLO	Reserved	POS	NEG	RESET_ STAT	ОТ	BUCK_ STATUS
Default	0	0	0	0	0	0	0	0
Туре	R	R	R	R	R	R	R	R

Bit	Name	Description			
7	PGOOD	1 : Buck is enabled and soft-start is completed.			
6	UVLO	1 : Signifies the VIN is less than the UVLO threshold.			
5	Reserved	Reserved bits			
4	POS	1 : Signifies a positive voltage transition is in progress			
3	NEG	1 : Signifies a negative voltage transition is in progress			
2	RESET_STAT	1 : Indicates that a register reset was performed.			
1	ОТ	1 : Signifies the thermal shutdown is active.			
0	BUCK_STATUS	1 : Buck enabled; 0 : buck disabled.			

Table 10. CONTROL2

	Address: 0x06 Description: Control2 setting							
Bit	7	6	5	4	3	2	1	0
Field		DN_SR[2:0]		Reserved	SS_S	R[1:0]	EN_ VSEL1	EN_ VSEL0
Default	0 1 1			0	0	0	1	1
Туре	R/W			R	R	W	R/W	R/W

Bit	Name	Description
7:5	DN_SR[2:0]	DVS speed for DN DVS 000 = 24mV step/µs 001 = 12mV step/µs 010 = 6mV step/µs 011 = 3mV step/µs 100 = 1.5mV step/µs 101 = 0.75mV step/µs 110 = 0.375mV step/µs 111 = 0.1875mV step/µs
4	Reserved	Reserved bits
3:2	SS_SR[1:0]	DVS speed for soft-start DVS 00 = 10mV step/µs 01 = 5mV step/µs 10 = 2.5mV step/µs 11 = 1.25mV step/µs
1	EN_VSEL1	0 : Disable 1 : Enable
0	EN_VSEL0	0 : Disable 1 : Enable

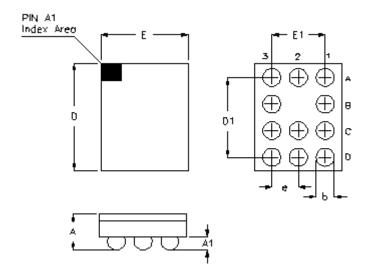
Table 11. CONTROL4

	Address: 0x08 Description: Control4 setting							
Bit	7	6	5	4	3	2	1	0
Field	Rese	erved			DIS_D	LY[5:0]		
Default	0	0	0 0 0 0 0 0					
Туре	R R/W							

Bit	Name	Description	
7:6	Reserved	Reserved bits	
5:0	DIS_DLY	Delay applied upon disable (ms) 000000b = 0ms - 111111b = 63ms (steps of 1ms)	



Outline Dimension



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Мах	Min.	Max	
A	0.500	0.600	0.020	0.024	
A1	0.170	0.230	0.007	0.009	
b	0.240	0.300	0.009	0.012	
D	1.580	1.660	0.062	0.065	
D1	1.2	200	0.0)47	
E	1.270	1.350	0.050	0.053	
E1	0.8	300	0.0)31	
е	0.4	100	0.0)16	

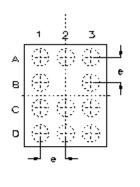
11B WL-CSP 1.31x1.62 Package (BSC)

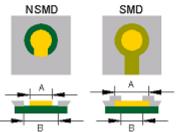
www.richtek.com



RT5721

Footprint Information



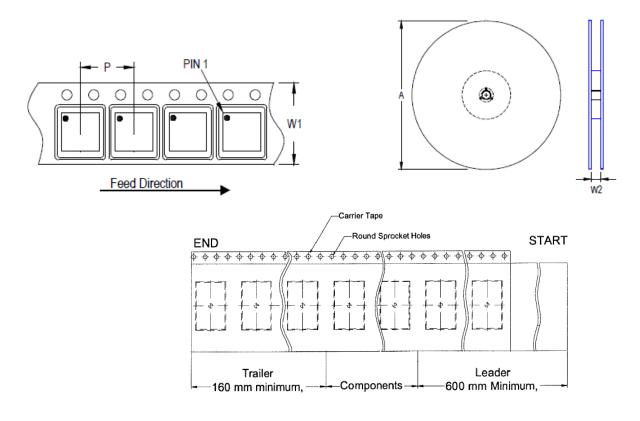


Deakage	Number	Turne	Footprir	nt Dimensio	on (mm)	Toloropoo
Package	of Pin	Туре	е	А	В	Tolerance
	11	NSMD	0.400	0.240	0.340	±0.025
WL-CSP1.31x1.62-11(BSC)	11	SMD		0.270	0.240	±0.025

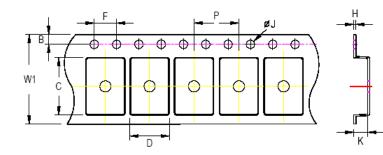


Packing Information

Tape and Reel Data



Package Type	Tape Size	Pocket Pitch	Reel Si	ze (A)	Units	Trailer	Leader	Reel Width (W2)
Package Type	(W1) (mm)	(P) (mm)	(mm)	(in)	per Reel	(mm)	(mm)	Min./Max. (mm)
WL-CSP 1.31x1.62	8	4	180	7	3,000	160	600	8.4/9.9



C, D and K are determined by component size. The clearance between the components and the cavity is as follows:

- For 8mm carrier tape: 0.5mm max.

Tape Size	W1	F	C	E	3	F	=	Ø	ίJ	Н
Tape Size	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.
8mm	8.3mm	3.9mm	4.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	0.6mm

RICHTEK is a registered trademark of Richtek Technology Corporation. Copyright © 2023 Richtek Technology Corporation. All rights reserved. www.richtek.com DS5721-00 November 2023

Tape and Reel Packing

Step	Photo/Description	Step	Photo/Description
1		4	
	Reel 7"		12 inner boxes per outer box
2		5	RICHTEK TATATATA
	Packing by Anti-Static Bag		Outer box Carton A
3		6	
	3 reels per inner box Box A		

Container	Reel		Вох				Carton			
Package	Size	Units	Item	Size(cm)	Reels	Units	Item	Size(cm)	Boxes	Unit
WL-CSP	7" 2.000		Box A	18.3*18.3*8.0	3	9,000	Carton A	38.3*27.2*38.3	12	108,000
1.31x1.62	1	3,000	Box E	18.6*18.6*3.5	1	3,000	For Combined or Partial Reel.			

Copyright © 2023 Richtek Technology Corporation. All rights reserved.



Packing Material Anti-ESD Property

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω/cm^2	10 ⁴ to 10 ¹¹					

Richtek Technology Corporation

14F, No. 8, Tai Yuen 1st Street, Chupei City Hsinchu, Taiwan, R.O.C. Tel: (8863)5526789

RICHTEK

Richtek products are sold by description only. Richtek reserves the right to change the circuitry and/or specifications without notice at any time. Customers should obtain the latest relevant information and data sheets before placing orders and should verify that such information is current and complete. Richtek cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Richtek product. Information furnished by Richtek is believed to be accurate and reliable. However, no responsibility is assumed by Richtek or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Richtek or its subsidiaries.

Copyright © 2023 Richtek Technology Corporation. All rights reserved. RICHTEK is a registered trademark of Richtek Technology Corporation.

www.richtek.com





Datasheet Revision History

Version	Date	Description	Item
00	2023/11/22	Final	